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The invention refers to the radio electronics and may be used in manufacturing the photodetectors and optoelectronic devices on base thereof.

Summary of the invention consists in the fact that in the process for obtaining the thin-filmed heterostructures on the A^2B^5 compound base, comprising a vacuum deposition of the strates in presence of the thermal gradient between the evaporator and the base, there is made a deposition of a strate with a narrow-zone component, treatment thereof in a salt solution, firing and etching and then the deposition of a strate with a wide-zone component.

The technical result consists in rising the charge carriers number.